# 2SC4593

### Silicon NPN Epitaxial

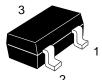
# **HITACHI**

### **Application**

UHF / VHF wide band amplifier

#### Outline

**CMPAK** 



- 1. Emitter
- 2. Base
- 3. Collector



### 2SC4593

### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	15	V
Collector to emitter voltage	$V_{\text{CEO}}$	9	V
Emitter to base voltage	$V_{EBO}$	1.5	V
Collector current	I <sub>c</sub>	50	mA
Collector power dissipation	P <sub>c</sub>	100	mW
Junction temperature	Тј	150	°C
Storage temperature	Tstg	-55 to +150	°C

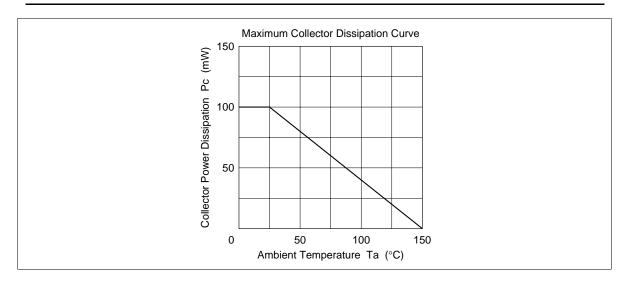
#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1	μΑ	V <sub>CB</sub> = 12 V, I <sub>E</sub> = 0
_	I <sub>CEO</sub>	_	_	1	mA	$V_{CE} = 9 \text{ V}, R_{BE} = \infty$
Emitter cutoff current	I <sub>EBO</sub>	_	_	10	μΑ	$V_{EB} = 1.5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub>	40	120	250	_	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Collector output capacitance	Cob	_	0.8	1.5	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0,$ f = 1MHz
Gain bandwidth product	f <sub>T</sub>	6.5	9.0	_	GHz	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Power gain	PG	9.5	12.5	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.2	2.5	dB	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA},$ f = 900 MHz

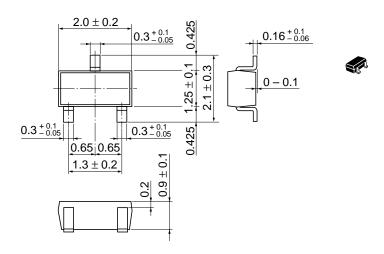
Note: Marking is "XM-".

See characteristic curve of 2SC4592

### 2SC4593







Hitachi Code	CMPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.006 g

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